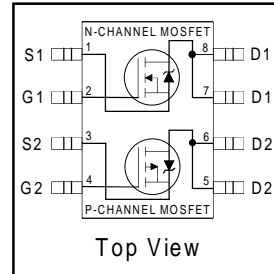


- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Fully Avalanche Rated

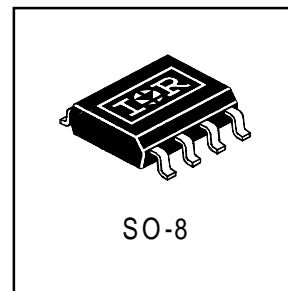
Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques.



	N-Ch	P-Ch
V_{DS}	20V	-20V
$R_{DS(on)}$	0.029Ω	0.058Ω



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

	Symbol	Maximum		Units	
		N-Channel	P-Channel		
Drain-Source Voltage	V_{DS}	20	-20	V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ^⑤	I_D	$T_A = 25^\circ\text{C}$	6.6	-5.3	A
		$T_A = 70^\circ\text{C}$	5.3	-4.3	
Pulsed Drain Current	I_{DM}	26	-21		
Continuous Source Current (Diode Conduction)	I_S	2.5	-2.5		
Maximum Power Dissipation ^⑤	P_D	$T_A = 25^\circ\text{C}$	2.0		W
		$T_A = 70^\circ\text{C}$	1.3		
Single Pulse Avalanche Energy	E_{AS}	100	150	mJ	
Avalanche Current	I_{AR}	4.1	-2.9	A	
Repetitive Avalanche Energy	E_{AR}	0.20		mJ	
Peak Diode Recovery dv/dt ^②	dv/dt	5.0	-5.0	V/ ns	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150 °C			

Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient ^⑤	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Conditions		
						Parameter	
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	N-Ch	20	—	—	V	V _{GS} = 0V, I _D = 250μA
		P-Ch	-20	—	—	—	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.027	—	V/°C	Reference to 25°C, I _D = 1mA
		P-Ch	—	0.031	—	—	Reference to 25°C, I _D = -1mA
R _{DS(ON)}	Static Drain-to-Source On-Resistance	N-Ch	—	0.023	0.029	Ω	V _{GS} = 4.5V, I _D = 6.0A ④
			—	0.030	0.046		V _{GS} = 2.7V, I _D = 5.2A ④
		P-Ch	—	0.049	0.058		V _{GS} = -4.5V, I _D = -2.9A ④
			—	0.082	0.098		V _{GS} = -2.7V, I _D = -1.5A ④
V _{GS(th)}	Gate Threshold Voltage	N-Ch	0.7	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
		P-Ch	-0.7	—	—	—	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	N-Ch	—	20	—	S	V _{DS} = 10V, I _D = 6.0A ④
		P-Ch	—	5.9	—	—	V _{DS} = -10V, I _D = -1.5A ④
I _{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	1.0	μA	V _{DS} = 16V, V _{GS} = 0V
		P-Ch	—	—	-1.0		V _{DS} = -16V, V _{GS} = 0V
		N-Ch	—	—	5.0		V _{DS} = 16V, V _{GS} = 0V, T _J = 55°C
		P-Ch	—	—	-25		V _{DS} = -16V, V _{GS} = 0V, T _J = 55°C
I _{GSS}	Gate-to-Source Forward Leakage	N-P	—	—	±100	nA	V _{GS} = ±12V
Q _g	Total Gate Charge	N-Ch	—	18	27	nC	N-Channel I _D = 6.0A, V _{DS} = 10V, V _{GS} = 4.5V ④
		P-Ch	—	19	29		
Q _{gs}	Gate-to-Source Charge	N-Ch	—	2.2	3.3	nC	P-Channel I _D = -2.9A, V _{DS} = -16V, V _{GS} = -4.5V ④
		P-Ch	—	4.0	6.1		
Q _{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	6.2	9.3	nC	P-Channel I _D = -2.9A, V _{DS} = -16V, V _{GS} = -4.5V ④
		P-Ch	—	7.7	12		
t _{d(on)}	Turn-On Delay Time	N-Ch	—	8.1	12	ns	N-Channel V _{DD} = 10V, I _D = 1.0A, R _G = 6.0Ω, R _D = 10Ω ④
P-Ch	—	15	22				
t _r	Rise Time	N-Ch	—	17	25	ns	P-Channel V _{DD} = -10V, I _D = -2.9A, R _G = 6.0Ω, R _D = 3.4Ω ④
		P-Ch	—	40	60		
t _{d(off)}	Turn-Off Delay Time	N-Ch	—	38	57	ns	P-Channel V _{DD} = -10V, I _D = -2.9A, R _G = 6.0Ω, R _D = 3.4Ω ④
		P-Ch	—	42	63		
t _f	Fall Time	N-Ch	—	31	47	ns	P-Channel V _{DD} = -10V, I _D = -2.9A, R _G = 6.0Ω, R _D = 3.4Ω ④
		P-Ch	—	49	73		
C _{iss}	Input Capacitance	N-Ch	—	900	—	pF	N-Channel V _{GS} = 0V, V _{DS} = 15V, f = 1.0MHz
		P-Ch	—	780	—		
C _{oss}	Output Capacitance	N-Ch	—	430	—	pF	P-Channel V _{GS} = 0V, V _{DS} = -15V, f = 1.0MHz
		P-Ch	—	470	—		
C _{rss}	Reverse Transfer Capacitance	N-Ch	—	200	—	pF	P-Channel V _{GS} = 0V, V _{DS} = -15V, f = 1.0MHz
		P-Ch	—	240	—		

Source-Drain Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Conditions		
						Parameter	
I _S	Continuous Source Current (Body Diode)	N-Ch	—	—	2.5	A	
		P-Ch	—	—	-2.5		
I _{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	26	A	
		P-Ch	—	—	-21		
V _{SD}	Diode Forward Voltage	N-Ch	—	0.72	1.0	V	T _J = 25°C, I _S = 1.7A, V _{GS} = 0V ③
		P-Ch	—	-0.78	-1.0		T _J = 25°C, I _S = -2.9A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	N-Ch	—	52	77	ns	N-Channel T _J = 25°C, I _F = 1.7A, di/dt = 100A/μs ④
		P-Ch	—	47	71		
Q _{rr}	Reverse Recovery Charge	N-Ch	—	58	86	nC	P-Channel T _J = 25°C, I _F = -2.9A, di/dt = 100A/μs ④
		P-Ch	—	49	73		

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 22)
- ② N-Channel I_{SD} ≤ 4.1A, di/dt ≤ 92A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ③ P-Channel I_{SD} ≤ -2.9A, di/dt ≤ -77A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ④ N-Channel Starting T_J = 25°C, L = 12mH R_G = 25Ω, I_{AS} = 4.1A. (See Figure 12)
- ⑤ P-Channel Starting T_J = 25°C, L = 35mH R_G = 25Ω, I_{AS} = -2.9A.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Surface mounted on FR-4 board, t ≤ 10sec.

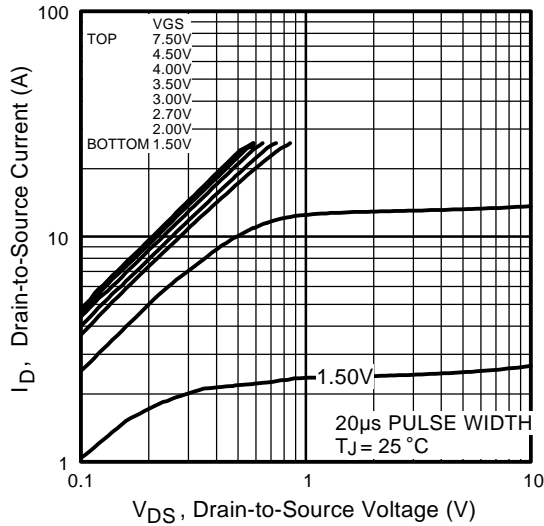


Fig 1. Typical Output Characteristics

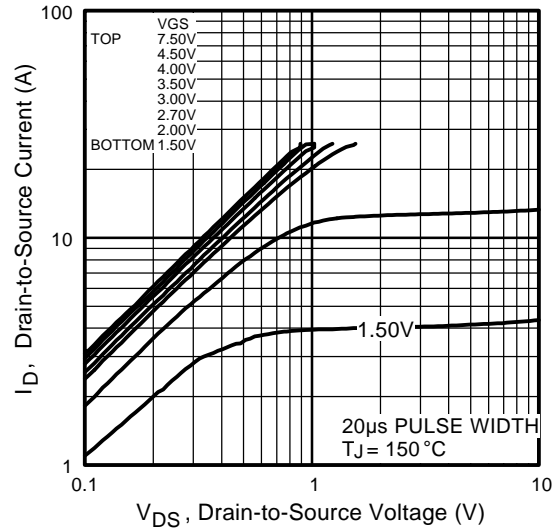


Fig 2. Typical Output Characteristics

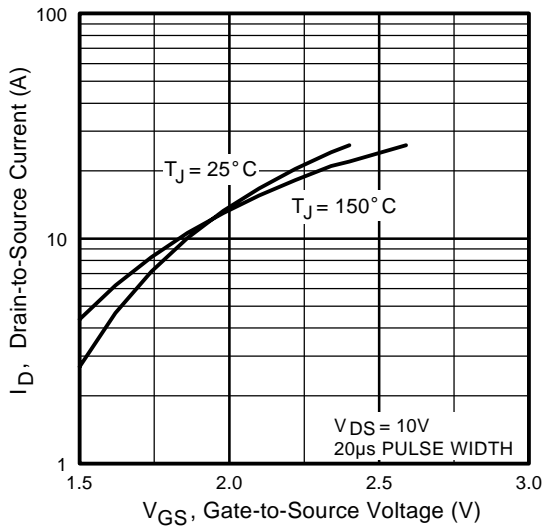


Fig 3. Typical Transfer Characteristics

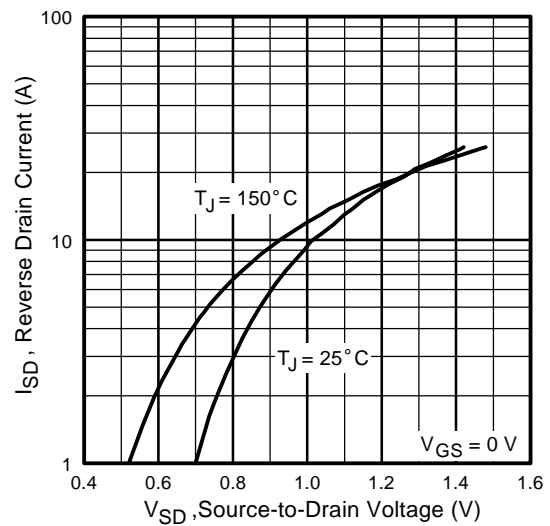


Fig 4. Typical Source-Drain Diode Forward Voltage

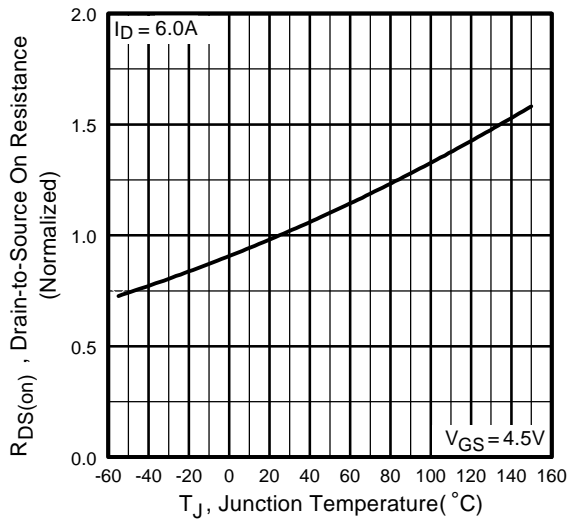


Fig 5. Normalized On-Resistance Vs. Temperature

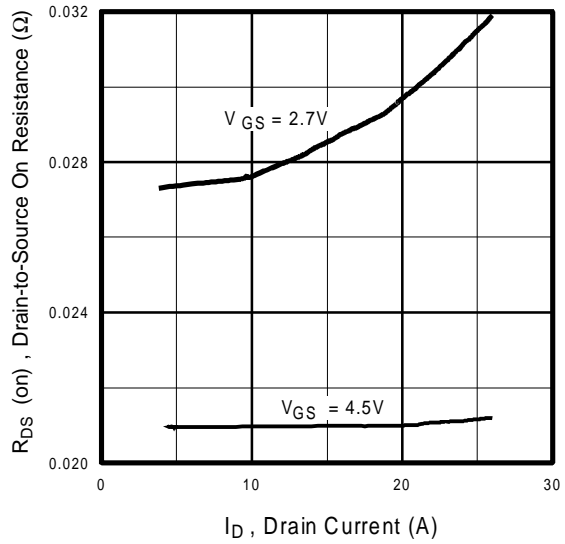


Fig 6. Typical On-Resistance Vs. Drain Current

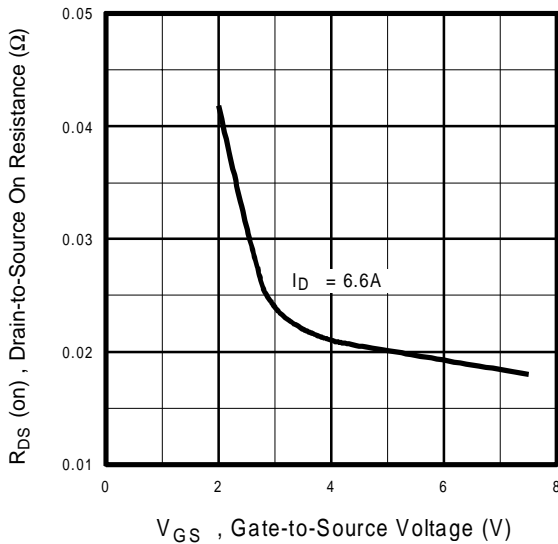


Fig 7. Typical On-Resistance Vs. Gate Voltage

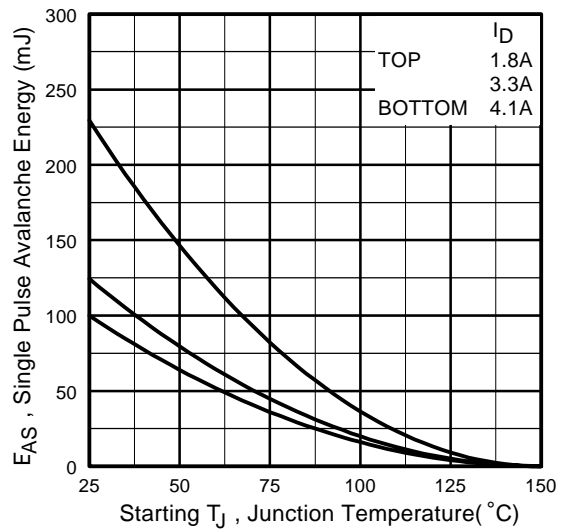


Fig 8. Maximum Avalanche Energy Vs. Drain Current

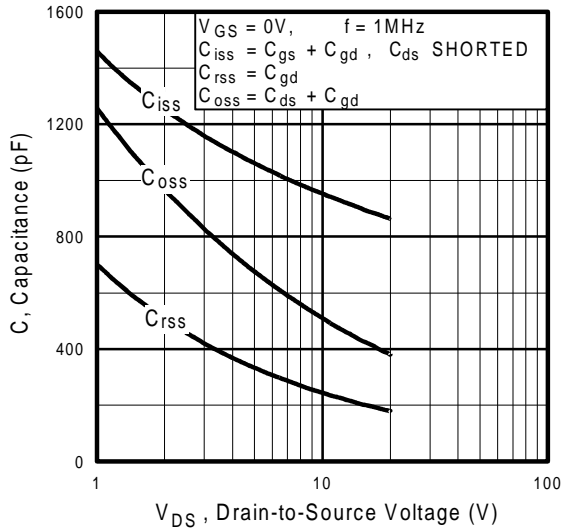


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

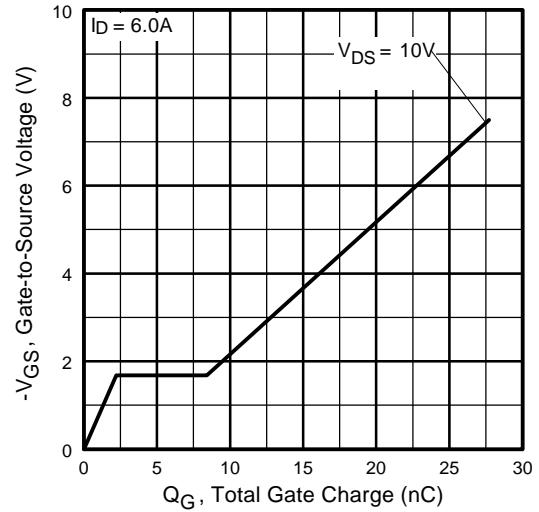


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

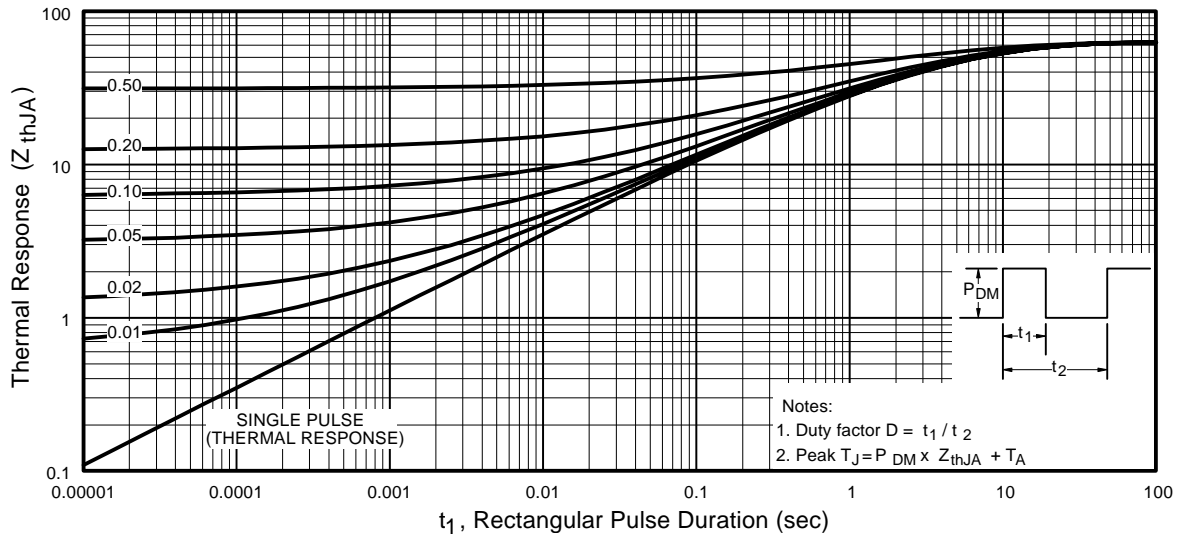


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

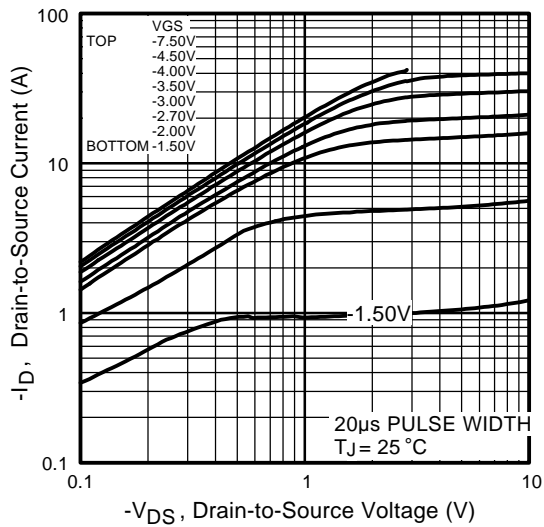


Fig 12. Typical Output Characteristics

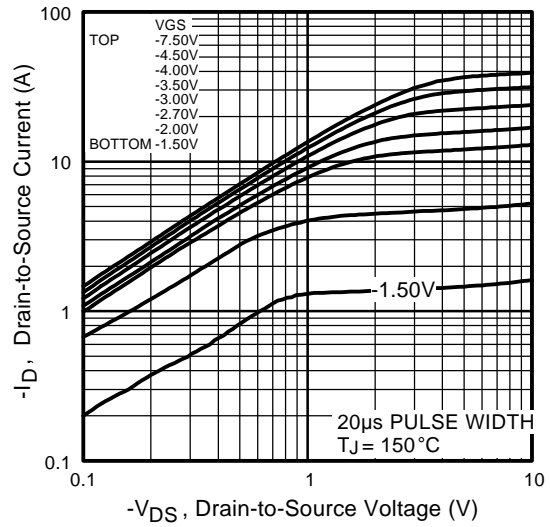


Fig 13. Typical Output Characteristics

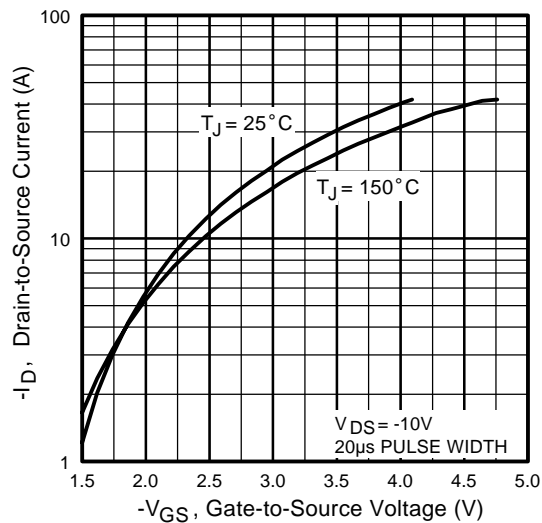


Fig 14. Typical Transfer Characteristics

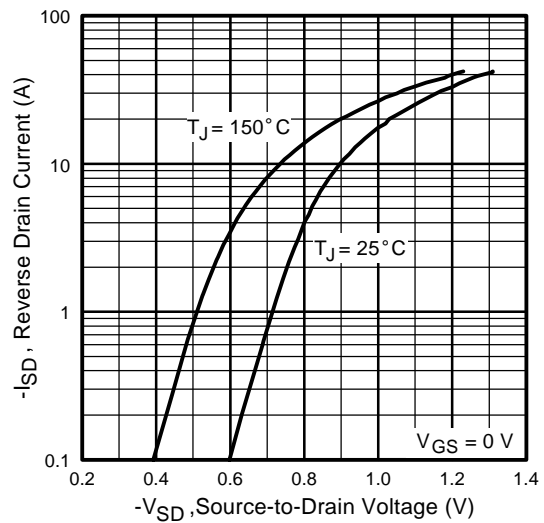


Fig 15. Typical Source-Drain Diode Forward Voltage

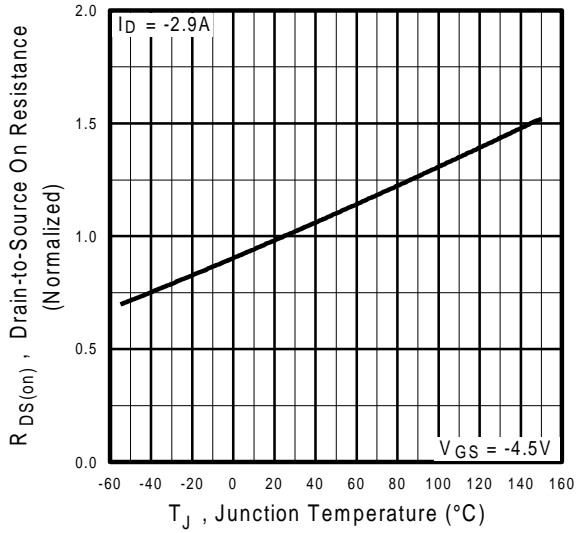


Fig 16. Normalized On-Resistance Vs. Temperature

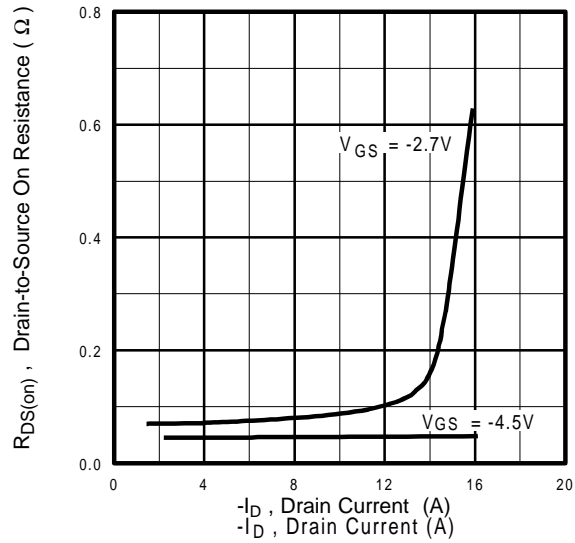


Fig 17. Typical On-Resistance Vs. Drain Current

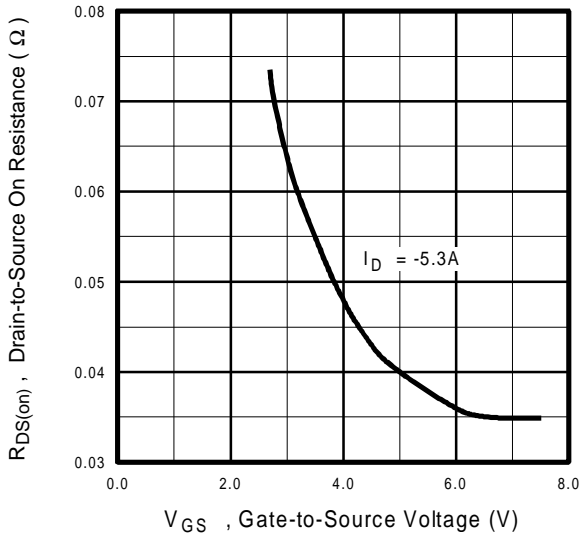


Fig 18. Typical On-Resistance Vs. Gate Voltage

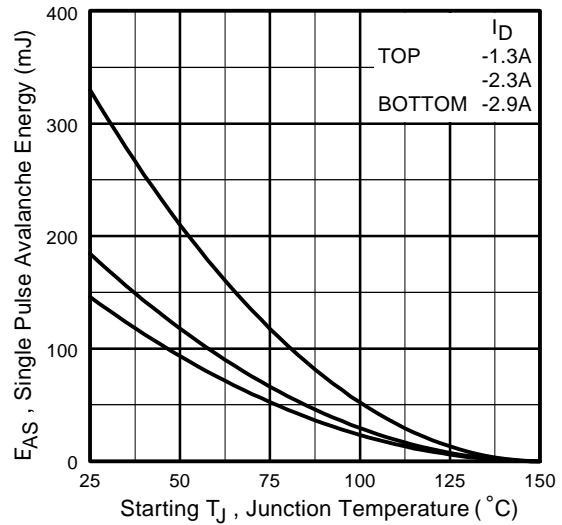


Fig 19. Maximum Avalanche Energy Vs. Drain Current

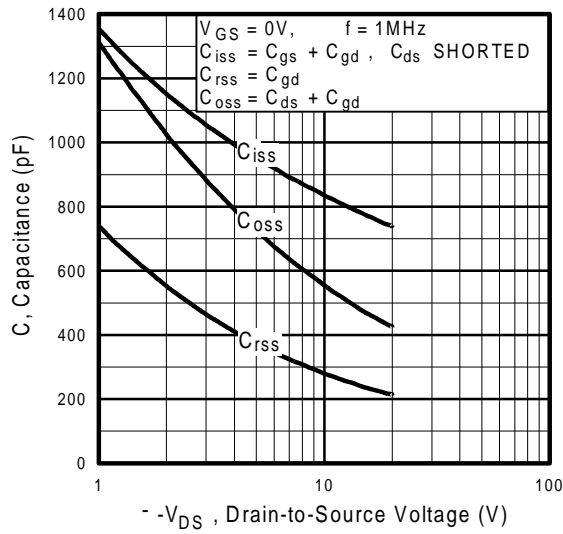


Fig 20. Typical Capacitance Vs. Drain-to-Source Voltage

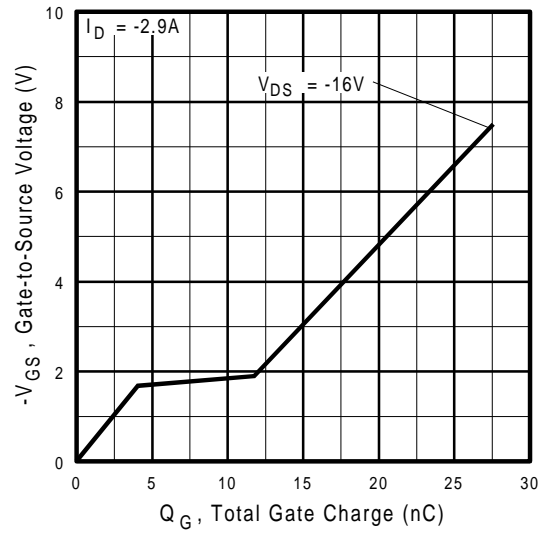


Fig 21. Typical Gate Charge Vs. Gate-to-Source Voltage

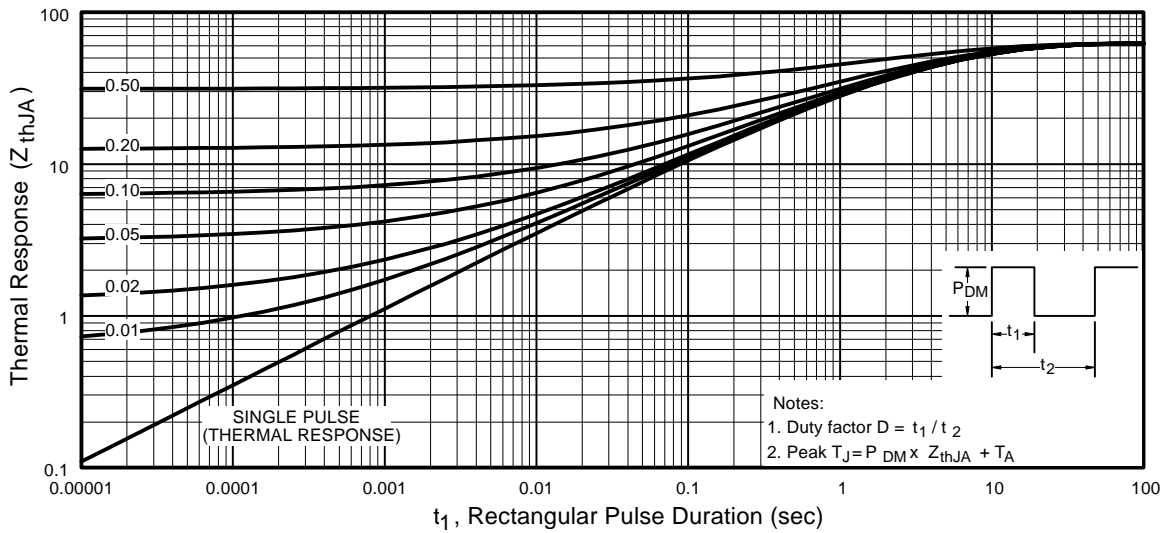
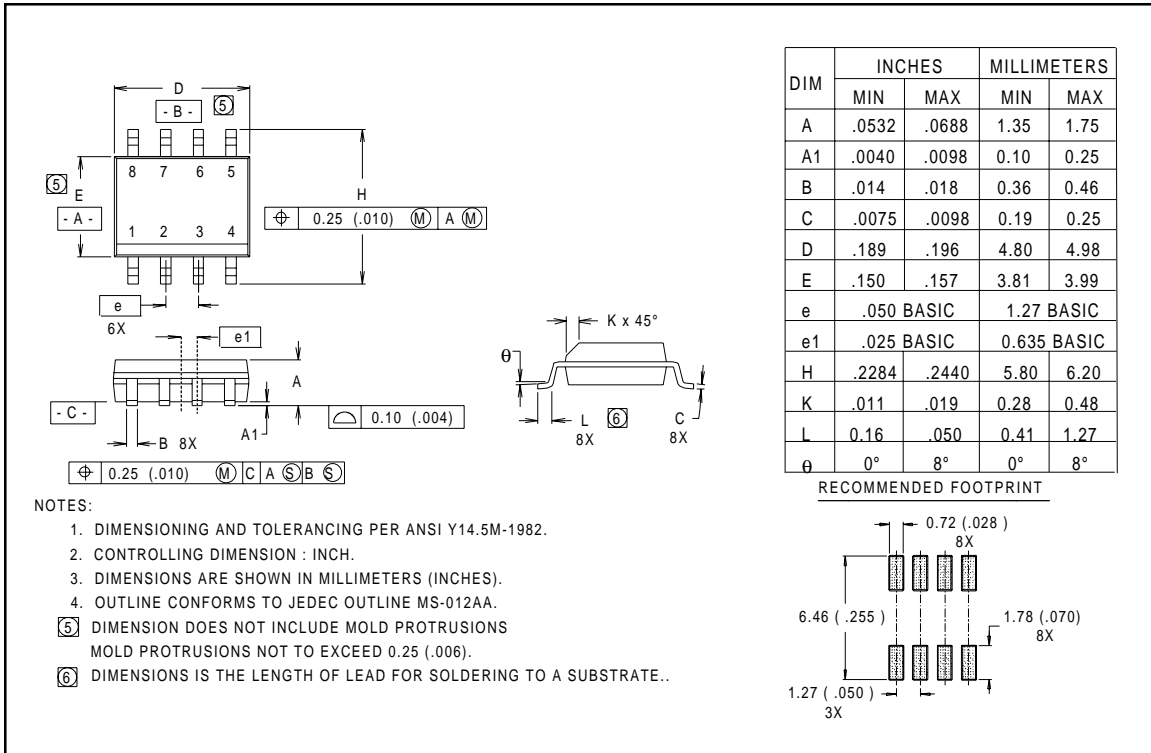


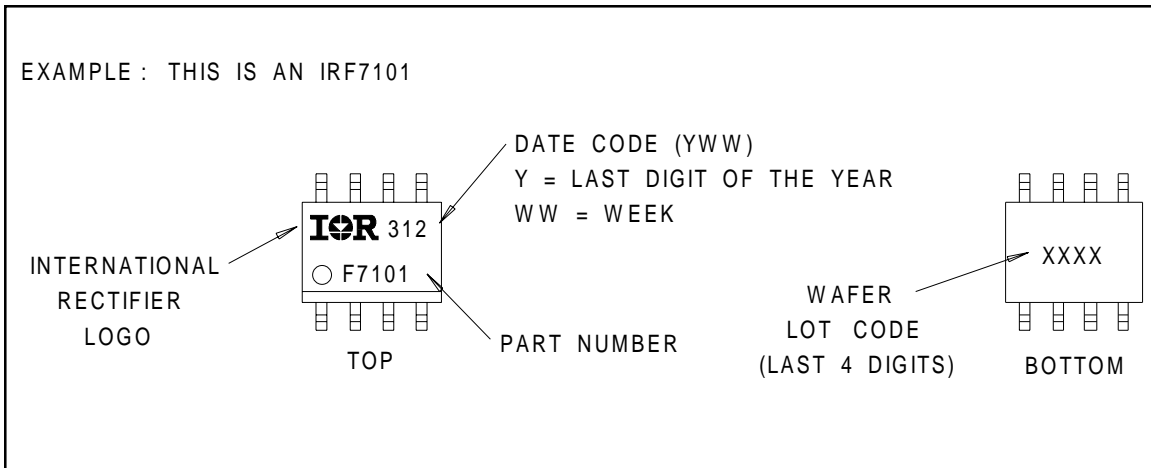
Fig 22. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Package Outline SO8 Outline



Part Marking Information

SO8



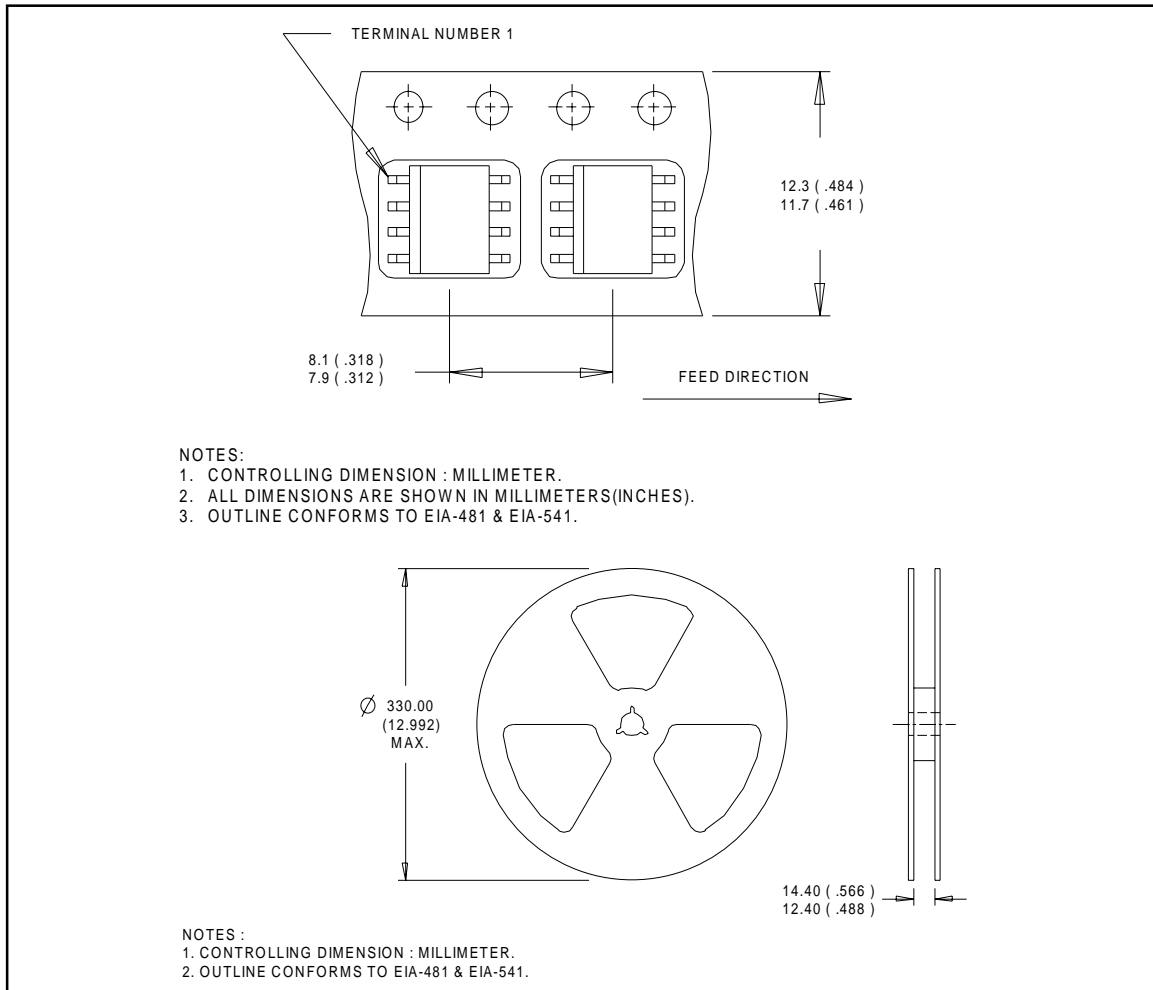
IRF7317

International
IR Rectifier

Tape & Reel Information

S08

Dimensions are shown in millimeters (inches)



International
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